

1. (Previously Presented) A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film,

wherein the first laser beam is a third harmonic of a first YAG laser, and

wherein the second laser beam is a second harmonic of a second YAG laser.

2. (Original) A method according to claim 1, wherein the first laser beam and the second laser beam are different in wavelength from each other.

3. (Previously Presented) A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film,

wherein the first laser beam is a YVO₄ laser, and

wherein the second laser beam is a YAG laser.

4. (Previously Presented) A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film,

wherein the second laser beam is 370 to 650 nm in wavelength, and

wherein the first laser beam is a YVO₄ laser.

5. (Original) A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a first laser beam to form a first crystalline semiconductor film; and

irradiating the first crystalline semiconductor film with a second laser beam to form a second crystalline semiconductor film,

wherein the first laser beam is 126 to 370 nm in wavelength whereas the second laser beam is 370 to 650 nm in wavelength.

6. (Previously Presented) A method according to claim 1, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

7. (Previously Presented) A method according to claim 1, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

8. (Previously Presented) A method according to claim 3, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

9. (Previously Presented) A method according to claim 3, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

10. (Previously Presented) A method according to claim 4, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

11. (Previously Presented) A method according to claim 4, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

12. (Previously Presented) A method according to claim 5, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

13. (Previously Presented) A method according to claim 5, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

14-41. (Canceled)

42. (New) A method of manufacturing a semiconductor device, comprising:
forming an amorphous semiconductor film over a substrate;
heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a first laser beam to form a second crystalline semiconductor film; and

irradiating the second crystalline semiconductor film with a second laser beam to form a third crystalline semiconductor film,

wherein the first laser beam is a third harmonic of a first YAG laser, and

wherein the second laser beam is a second harmonic of a second YAG laser.

43. (New) A method according to claim 42, wherein the first laser beam and the second laser beam are different in wavelength from each other.

44. (New) A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a first laser beam to form a second crystalline semiconductor film; and

irradiating the second crystalline semiconductor film with a second laser beam to form a third crystalline semiconductor film,

wherein the first laser beam is a YVO₄ laser, and

wherein the second laser beam is a YAG laser.

45. (New) A method of manufacturing a semiconductor device, comprising:

forming an amorphous semiconductor film over a substrate;

heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a first laser beam to form a second crystalline semiconductor film; and

irradiating the second crystalline semiconductor film with a second laser beam to form a third crystalline semiconductor film,

wherein the second laser beam is 370 to 650 nm in wavelength, and

wherein the first laser beam is a YVO₄ laser.

46. (New) A method of manufacturing a semiconductor device, comprising the steps of:

forming an amorphous semiconductor film over a substrate;

heating the amorphous semiconductor film to form a first crystalline semiconductor film;

irradiating the first crystalline semiconductor film with a first laser beam to form a second crystalline semiconductor film; and

irradiating the second crystalline semiconductor film with a second laser beam to form a third crystalline semiconductor film,

wherein the first laser beam is 126 to 370 nm in wavelength whereas the second laser beam is 370 to 650 nm in wavelength.

47. (New) A method according to claim 42, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

48. (New) A method according to claim 42, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

49. (New) A method according to claim 44, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

50. (New) A method according to claim 44, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

51. (New) A method according to claim 45, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

52. (New) A method according to claim 45, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

53. (New) A method according to claim 46, wherein the semiconductor device is incorporated into a device selected from the group consisting of a liquid crystal display device and a light emitting device.

54. (New) A method according to claim 46, wherein the semiconductor device is incorporated into a device selected from the group consisting of a cellular phone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.